

SEMICONDUCTOR
TECHNICAL DATA

KTC4373

EPITAXIAL PLANAR NPN TRANSISTOR

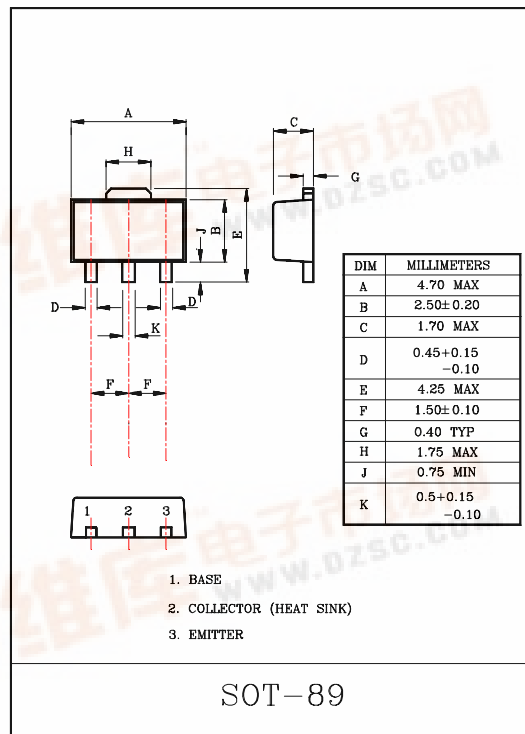
HIGH VOLTAGE APPLICATION.

FEATURES

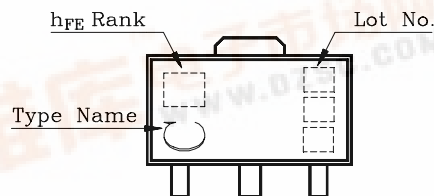
- High Voltage : $V_{CEO}=120V$.
- High Transition Frequency : $f_T=120MHz$.
- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTA1661.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	500	mW
	$P_C *$	1	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^{\circ}C$

 $P_C *$: KTC4373 mounted on ceramic substrate (250mm²x0.8t)

Marking

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=120V, I_E=0$	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=5V, I_C=100mA$	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=500mA$	-	-	1.0	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=100mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	-	30	pF

Note: f_T Classification O:80~160, Y:120~240

KTC4373

